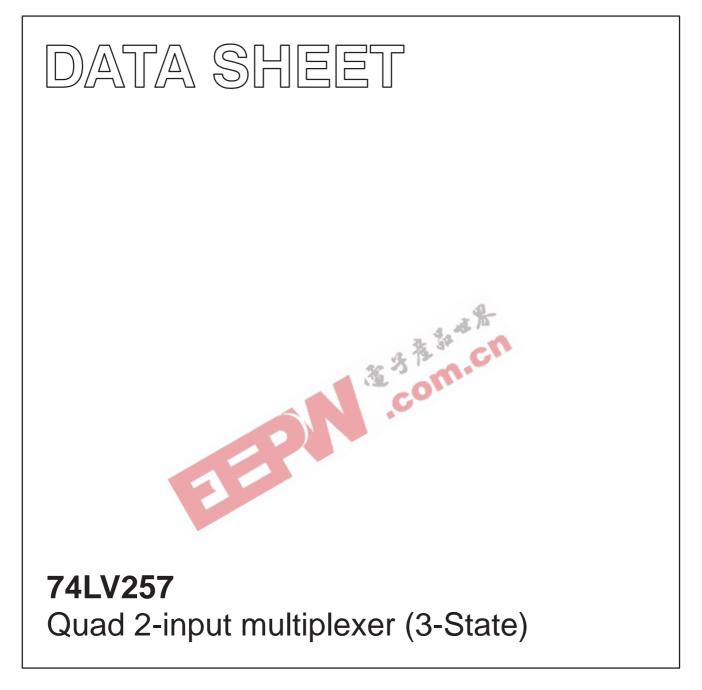
INTEGRATED CIRCUITS



Product specification Supersedes data of 1997 Jun 06 IC24 Data Handbook 1998 May 20



74LV257

FEATURES

- Optimized for low voltage applications: 1.0 to 3.6 V
- \bullet Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$
- Non-inverting data path
- Output capability: bus driver
- I_{CC} category: MSI

DESCRIPTION

The 74LV257 is a low-voltage Si-gate CMOS device and is pin and function compatible with 74HC/HCT257.

The 74LV257 is a quad 2-input multiplexer with 3-state outputs, which select 4 bits of data from two sources and are controlled by a common data select input (S). The data inputs from source 0 ($1I_0$ to $4I_0$) are selected when input S is LOW and the data inputs from source 1 (111 to 4l1) are selected when S in HIGH. Data appears at the outputs (1Y to 4Y) in true (non-inverting) from the selected inputs. The 74LV257 is the logic implementation of a 4-pole, 2-position switch, where the position of the switch is determined by the logic levels applied to S. The outputs are forced to a high impedance OFF-state when OE is HIGH.

The logic equations for the outputs are: $1Y = \overline{OE} \times (1I_1 \times S + 1I_0 \times \overline{S})$ $2\mathsf{Y} = \overline{\mathsf{OE}} \times (2\mathsf{I}_1 \times \mathsf{S} + 2\mathsf{I}_0 \times \overline{\mathsf{S}})$ $3Y = \overline{OE} \times (3I_1 \times S + 3I_0 \times \overline{S})$ $4\mathsf{Y} = \overline{\mathsf{OE}} \times (4\mathsf{I}_1 \times \mathsf{S} + 4\mathsf{I}_0 \times \overline{\mathsf{S}})$

QUICK REFERENCE DATA

GND = 0.V T_{omb} = 25°C t_r = t_f < 2.5 ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT	
t _{PHL} /t _{PLH}	Propagation delay nl ₀ , nl ₁ to nY S to nY	C _L = 15 pF; V _{CC} = 3.3 V	10 14	ns	
Cl	Input capacitance		3.5	pF	
C _{PD}	Power dissipation capacitance per gate	$V_{I} = GND$ to V_{CC}^{1}	30	pF	

NOTE:

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W) P_D = C_{PD} × V_{CC}² × f_i + \sum (C_L × V_{CC}² × f_o) where: f_i = input frequency in MHz; C_L = output load capacitance in pF; f_o = output frequency in MHz; V_{CC} = supply voltage in V; ∇ (C × V(-2 × f) = output frequency of the output frequency o

 $\sum (C_L \times V_{CC}^2 \times f_0) = \text{sum of the outputs.}$

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
16-Pin Plastic DIL	-40°C to +125°C	74LV257 N	74LV257 N	SOT38-4
16-Pin Plastic SO	-40°C to +125°C	74LV257 D	74LV257 D	SOT109-1
16-Pin Plastic SSOP Type II	-40°C to +125°C	74LV257 DB	74LV257 DB	SOT338-1
16-Pin Plastic TSSOP Type I	-40°C to +125°C	74LV257 PW	74LV257PW DH	SOT403-1

PIN CONFIGURATION

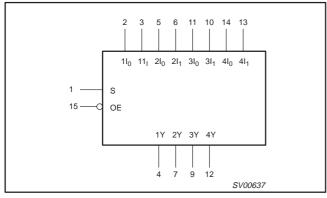
S 1	16 V _{CC}
1I ₀ 2	15 OE
1I ₁ 3	14 4I ₀
IY 4	13 4l ₁
2l ₀ 5	12 4Y
2l ₁ 6	11 3I ₀
2Y 7	10 3I ₁
GND 8	9 3Y
	SV00636

PIN DESCRIPTION

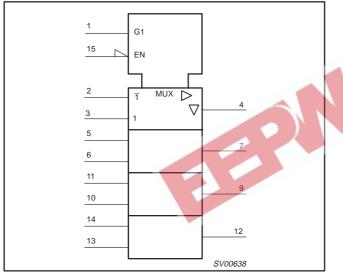
PIN NUMBER	SYMBOL	FUNCTION			
1	S	Common data select input			
2, 5, 11, 14	$1I_0$ to $4I_0$	Data inputs from source 0			
3, 6, 10, 13	1l ₁ to 4l ₁	Data inputs from source 1			
4, 7, 9, 12	1Y to 4Y	3-state multiplexer outputs			
8	GND	Ground (0 V)			
15	OE	3-State output enable input (active LOW)			
16	V _{CC}	Positive supply voltage			

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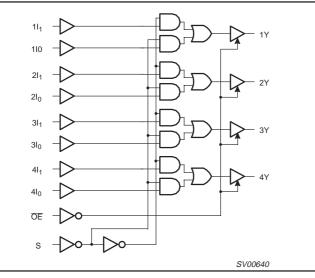
LOGIC SYMBOL

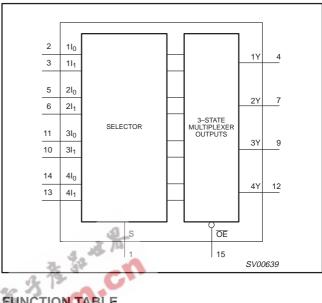


LOGIC SYMBOL (IEEE/IEC)



LOGIC DIAGRAM





FUNCTIONAL DIAGRAM

FUNCTION TABLE

C	INPUTS							
OE	S	nl ₀	nl ₁	nY				
Н	Х	Х	Х	Z				
L	Н	Х	L	L				
L	Н	Х	Н	н				
L	L	L	Х	L				
L	L	Н	Х	Н				

NOTES:

HIGH voltage level LOW voltage level

H = L = X = Z = don't care

high impedance OFF-state

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	PARAMETER CONDITIONS				UNIT
V _{CC}	DC supply voltage	upply voltage See Note 1				V
VI	Input voltage		0	-	V _{CC}	V
Vo	Output voltage		0	-	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics	-40 -40		+85 +125	°C
t _r , t _f	Input rise and fall times	$V_{CC} = 1.0V \text{ to } 2.0V$ $V_{CC} = 2.0V \text{ to } 2.7V$ $V_{CC} = 2.7V \text{ to } 3.6V$	- - -		500 200 100	ns/V

NOTE:

1. The LV is guaranteed to function down to V_{CC} = 1.0V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2V to V_{CC} =3.6V.

-

ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage	32 3	-0.5 to +4.6	V
$\pm I_{\text{IK}}$	DC input diode current	$V_{\rm I} < -0.5 \text{ or } V_{\rm I} > V_{\rm CC} + 0.5 V$	20	mA
$\pm I_{OK}$	DC output diode current	$V_{\rm O} < -0.5$ or $V_{\rm O} > V_{\rm CC} + 0.5V$	50	mA
$\pm I_{O}$	DC output source or sink current – bus driver outputs	$-0.5V < V_{O} < V_{CC} + 0.5V$	35	mA
$^{\pm I_{GND},}_{\pm I_{CC}}$	DC V _{CC} or GND current for types with – bus driver outputs		70	mA
T _{stg}	Storage temperature range		-65 to +150	°C
PTOT PTOT PTOT Power dissipation per package – plastic DIL – plastic mini-pack (SO) – plastic shrink mini-pack (SSOP and TSSOP)		for temperature range: -40 to +125°C above +70°C derate linearly with 12 mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

NOTES:

Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

					LIMITS				
SYMBOL	PARAMETER	TEST CONDITIONS	-40	°C to +8	5°C	-40°C to	o +125°C	Тими Т	
			MIN	TYP ¹	MAX	MIN	MAX	1	
		$V_{CC} = 1.2 V$	0.9			0.9			
VIH	HIGH level Input voltage	$V_{CC} = 2.0 V$	1.4			1.4		V	
	, enage	$V_{CC} = 2.7 \text{ to } 3.6 \text{ V}$	2.0			2.0		1	
		$V_{CC} = 1.2 V$			0.3		0.3		
VIL	LOW level Input voltage	$V_{CC} = 2.0 V$			0.6		0.6	V	
	i enage	V_{CC} = 2.7 to 3.6 V			0.8		0.8]	
		V_{CC} = 1.2 V; V_I = V_{IH} or $V_{IL;}$ – I_O = 100 μ A		1.2					
V	HIGH level output	V_{CC} = 2.0 V; V_I = V_{IH} or V_{IL} ; $-I_O$ = 100 μ A	1.8	2.0		1.8		v	
V _{OH}	voltage; all outputs	V_{CC} = 2.7 V; V_{I} = V_{IH} or $V_{IL;}$ –I_O = 100 μA	2.5	2.7		2.5] `	
		V_{CC} = 3.0 V; V_I = V_{IH} or $V_{IL;}$ –I_O = 100 μA	2.8	3.0	-	2.8]	
V _{OH}	HIGH level output voltage; BUS driver outputs	V_{CC} = 3.0 V; V_I = V_{IH} or V_{IL} ; $-I_O$ = 8mA	2.40	2.82	n	2.20		V	
		V_{CC} = 1.2 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0					
M	LOW level output	$V_{CC} = 2.0 \text{ V}; \text{ V}_{I} = V_{IH} \text{ or } V_{IL}; I_{O} = 100 \mu \text{A}$	~0	0	0.2		0.2	V	
V _{OL}	voltage; all outputs	V_{CC} = 2.7 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0	0.2		0.2		
		V_{CC} = 3.0 V; V_{I} = V_{IH} or V_{IL} ; I_{O} = 100 μ A		0	0.2		0.2]	
V _{OL}	LOW level output voltage; BUS driver outputs	V_{CC} = 3.0 V; V_I = V_{IH} or V_{IL} ; I_O = 8mA		0.20	0.40		0.50	V	
lı	Input leakage current	$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = V_{CC} \text{ or GND}$			1.0		1.0	μA	
I _{OZ}	3-State output OFF-state current	$V_{CC} = 3.6 V; V_I = V_{IH} \text{ or } V_{IL};$ $V_O = V_{CC} \text{ or GND}$			5		10	μΑ	
I _{CC}	Quiescent supply current; MSI	V_{CC} = 3.6 V; V_{I} = V_{CC} or GND; I_{O} = 0			20.0		160	μΑ	
ΔI_{CC}	Additional quiescent supply current per input	V_{CC} = 2.7 V to 3.6 V; V_{I} = V_{CC} – 0.6 V			500		850	μA	

NOTE: 1. All typical values are measured at $T_{amb} = 25^{\circ}C$.

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AC CHARACTERISTICS

GND = 0V; $t_r = t_f \le 2.5 \text{ns}$; $C_L = 50 \text{pF}$; $R_L = 1 \text{K}\Omega$

			CONDITION			LIMITS			
SYMBOL	PARAMETER	WAVEFORM	CONDITION	-	40 to +85 °	С	-40 to -	+125 °C	UNIT
			V _{CC} (V)	MIN	TYP ¹	MAX	MIN	MAX	
			1.2		65				
t _{PHL} /t _{PLH} Propagation delay nl ₀ to nY nl ₁ to nY		Eisung 4	2.0		22	43		51	
		Figure 1	2.7		16	31		38	ns
			3.0 to 3.6		12 ²	25		30	
	Propagation delay S to nY	Figure 1	1.2		85				
t			2.0		29	56		66	ns
t _{PHL} /t _{PLH}			2.7		21	41		49	
			3.0 to 3.6		16 ²	33		39	
			1.2		60				ns
tanutan	3-State output enable time	Figure 2	2.0		20	39		46	
t _{PZH} /t _{PZL}	OE to nY	rigute z	2.7	4.3	15	29		34	115
			3.0 to 3.6	E 4	11 ²	23		27	
			1.2		65				
	3-State output disable time	Eiguro 2	2.0		24	40		49	ns
t _{PHZ} /t _{PLZ}	OE to nY	Figure 2	2.7		18	32		37	
			3.0 to 3.6		14 ²	26		30	

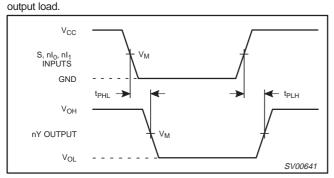
NOTES:

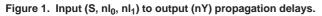
1. Unless otherwise stated, all typical values are measured at $T_{amb} = 25^{\circ}C$

2. Typical values are measured at V_{CC} = 3.3 V.

AC WAVEFORMS

 $\begin{array}{l} V_M = 0.5 \times V_{CC} \mbox{ at } V_{CC} < 2.7 \ V \\ V_M = 1.5 \ V \mbox{ at } V_{CC} \geq 2.7 \ V \\ V_X = V_{OL} + 0.3 \ V \mbox{ at } V_{CC} \geq 2.7 \ V \\ V_X = V_{OL} + 0.1 \times V_{CC} \mbox{ at } V_{CC} < 2.7 \ V \\ V_Y = V_{OH} - 0.3 \ V \mbox{ at } V_{CC} \geq 2.7 \ V \\ V_Y = V_{OH} - 0.3 \ V \mbox{ at } V_{CC} \geq 2.7 \ V \\ V_Q = 0.1 \times V_{CC} \mbox{ at } V_{CC} < 2.7 \ V \\ V_{OL} \mbox{ and } V_{OH} \mbox{ are the typical output voltage drop that occur with the submotion} \end{array}$





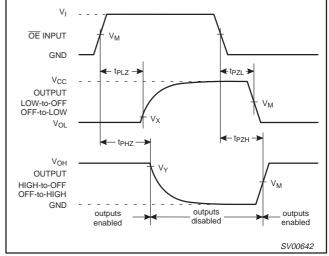
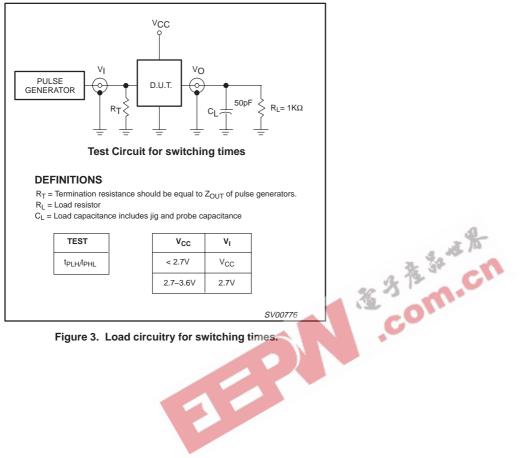
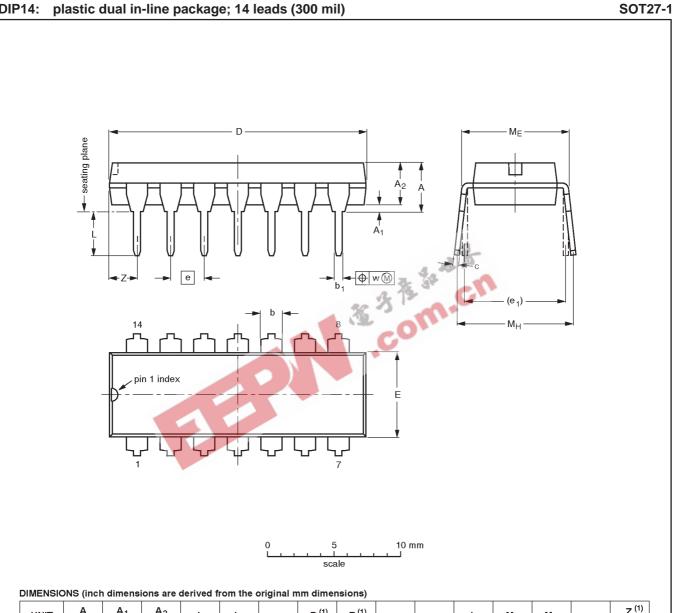


Figure 2. 3-State enable and disable times.

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TEST CIRCUIT





DIP14: plastic dual in-line package; 14 leads (300 mil)

DIMENSIC	DNS (inch	n dimens	ions are	derived f	rom the c	original n	nm dimer	isions)	
	Δ	Δ.	Δ.				- (1)	- (1)	

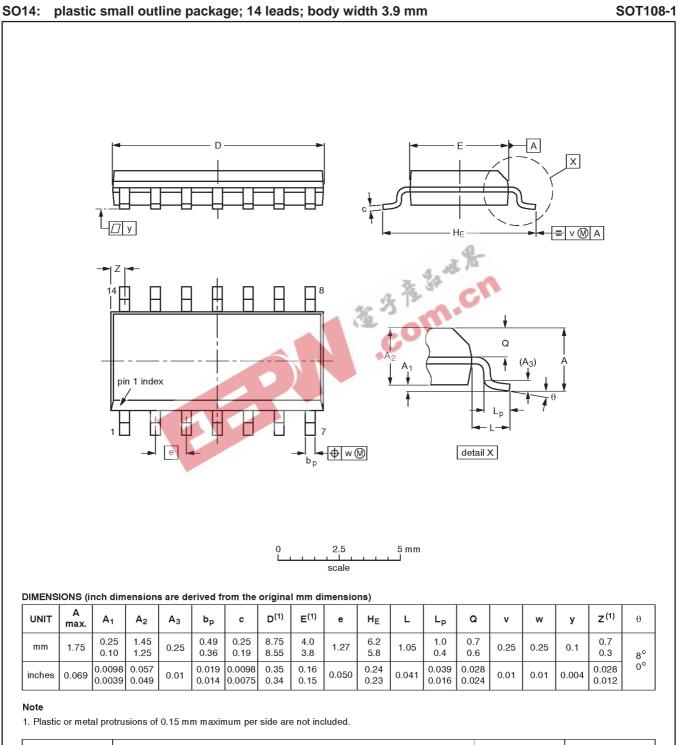
UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	ME	M _H	w	Z () max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

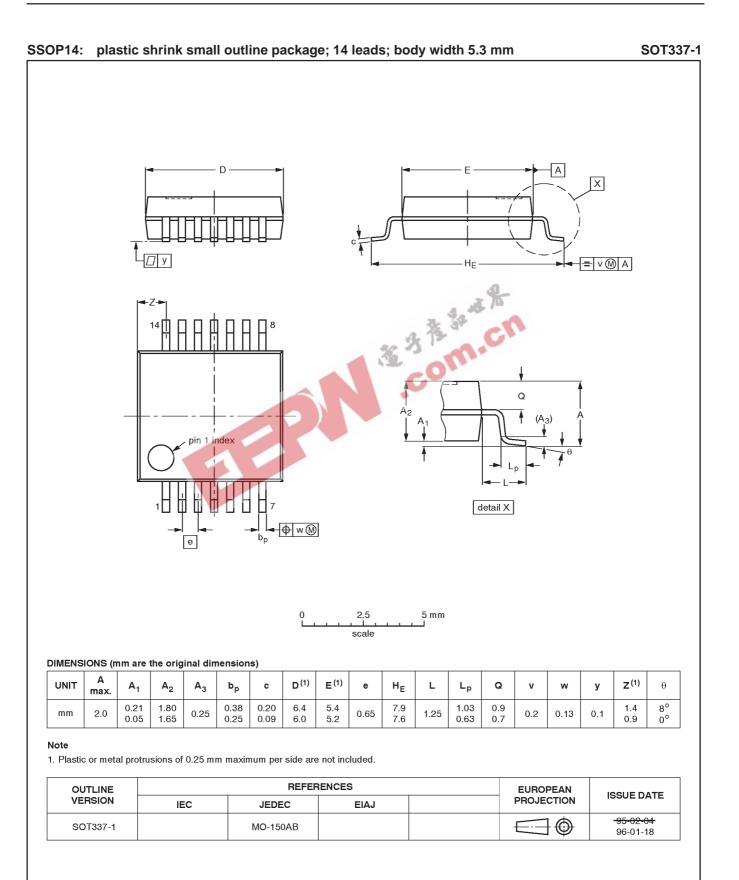
OUTLINE	UTLINE REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT27-1	050G04	MO-001AA			-92-11-17- 95-03-11	

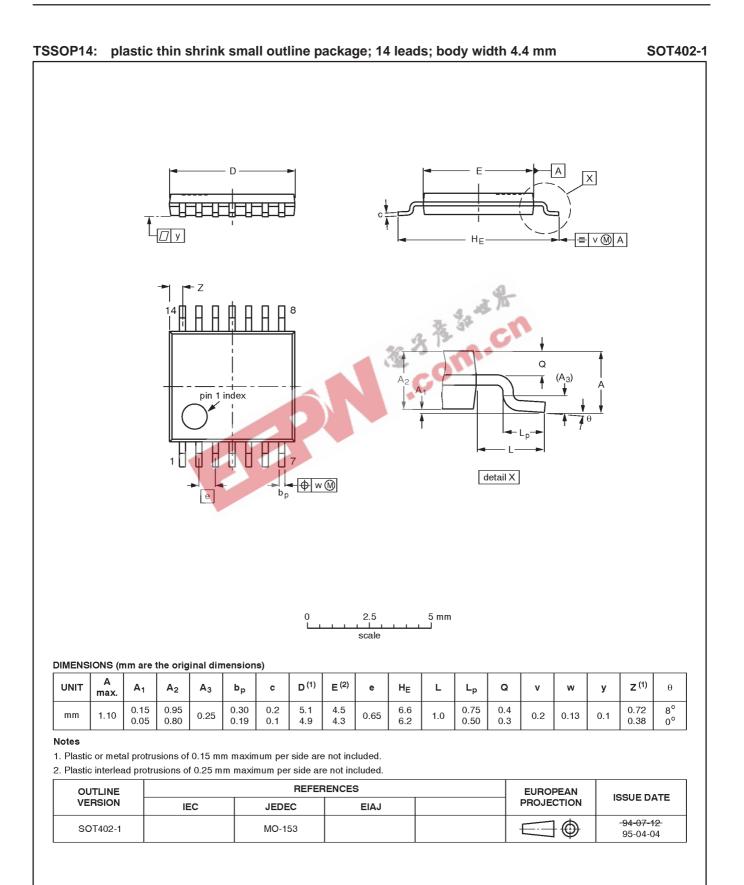
Product specification



74LV257

Product specification





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DEFINITIONS		
Data Sheet Identification	Product Status	Definition
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.
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